

Description

The HX205148 is a 140-watt capable, highly rugged, unmatched LDMOS FET, designed for wide-band commercial and industrial applications with frequencies HF to 1 GHz.

•Typical Performance (On fixture with device soldered):

$V_{DD} = 28$ Volts, $I_{DQ} = 800$ mA, CW.

Frequency	Gp (dB)	P _{-1dB} (W)	$\eta_D@P_{-1}$ (%)
1000 MHz	18	140	60

Features

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- Excellent thermal stability, low HCI drift
- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

Suitable Applications

- 2-30MHz (HF or Short wave communication)
- 30-88MHz (Ground communication)
- 54-88MHz (TV VHF I)
- 88-108MHz (FM)
- 118 -140MHz (Avionics)
- 136-174MHz (Commercial ground communication)
- 160-230MHz (TV VHF III)
- 30-512MHz (Jammer, Ground/Air communication)
- 470-860MHz (TV UHF)
- 100kHz - 1000MHz (ISM, instrumentation)

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	+95	Vdc
Gate--Source Voltage	V_{GS}	-10 to +10	Vdc
Operating Voltage	V_{DD}	+40	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_C = 85^\circ\text{C}$, $T_J = 200^\circ\text{C}$, DC test	$R_{\theta JC}$	0.4	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22--A114)	Class 2

Table 4. Electrical Characteristics ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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DC Characteristics (per half section)

Drain-Source Voltage $V_{GS}=0, I_{DS}=1.0mA$	$V_{(BR)DSS}$	95			V
Zero Gate Voltage Drain Leakage Current $(V_{DS} = 75V, V_{GS} = 0 V)$	I_{DSS}	—	—	1	μA
Zero Gate Voltage Drain Leakage Current $(V_{DS} = 28 V, V_{GS} = 0 V)$	I_{DSS}	—	—	1	μA
Gate--Source Leakage Current $(V_{GS} = 10 V, V_{DS} = 0 V)$	I_{GSS}	—	—	1	μA
Gate Threshold Voltage $(V_{DS} = 28V, I_D = 400 \mu A)$	$V_{GS(th)}$	—	2.2	—	V
Gate Quiescent Voltage $(V_{DD} = 28 V, I_D = 800 mA, \text{Measured in Functional Test})$	$V_{GS(Q)}$	—	3.1	—	V
Common Source Input Capacitance $(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	C_{ISS}		70		pF
Common Source Output Capacitance $(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	C_{OSS}		29.5		pF
Common Source Feedback Capacitance $(V_{GS} = 0V, V_{DS} = 28 V, f = 1 MHz)$	C_{RSS}		1.1		pF

Functional Tests (In Demo Test Fixture, 50 ohm system) $V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 1000 MHz, CW$ Signal Measurements.

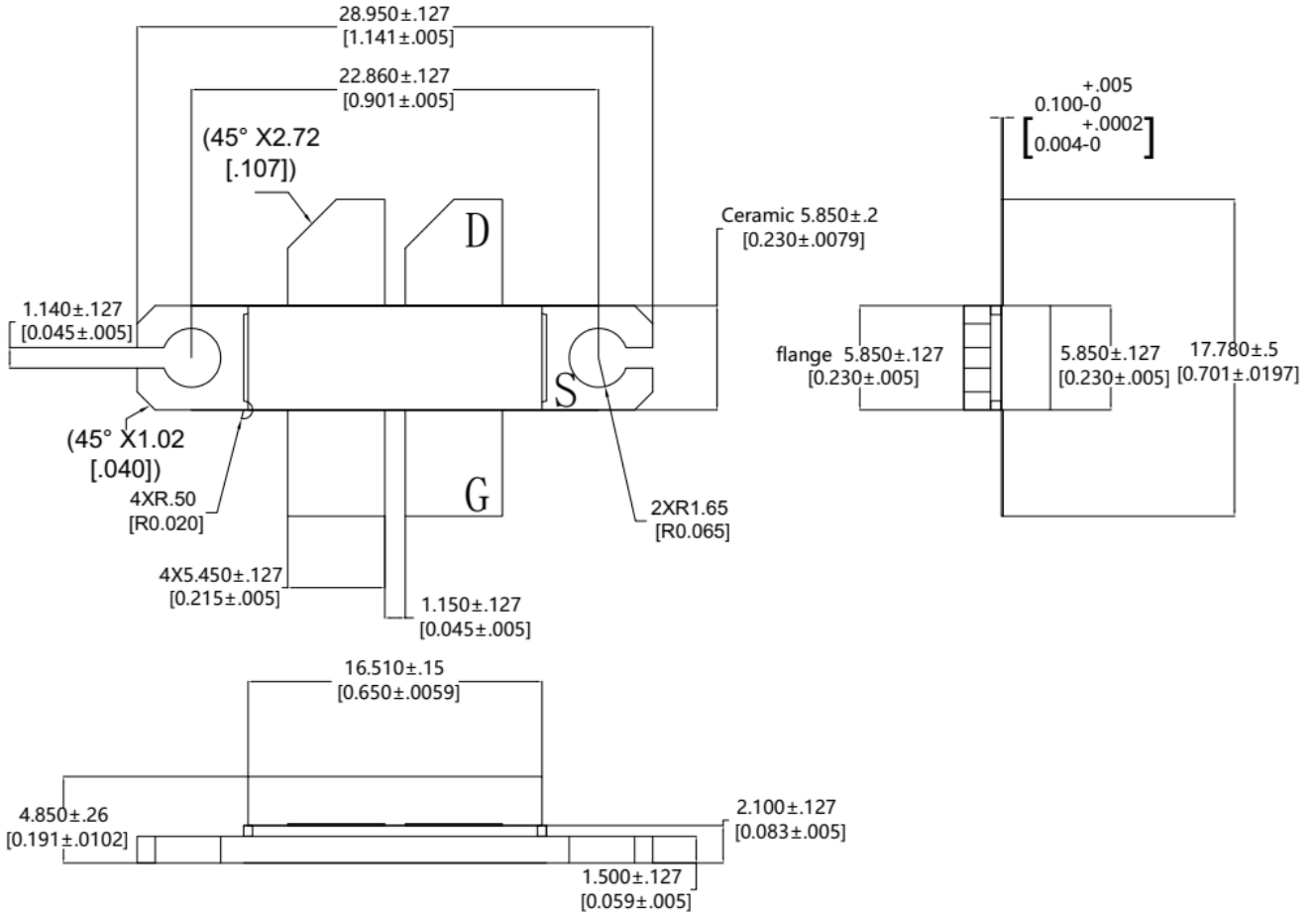
Power Gain	G_p	—	18	—	dB
Drain Efficiency@P1dB	η_D	—	60	—	%
1 dB Compression Point	P_{-1dB}	—	140	—	W
Input Return Loss	IRL	—	-7	—	dB

Load Mismatch (In Test Fixture, 50 ohm system): $V_{DD} = 28 Vdc, I_{DQ} = 800 mA, f = 1000 MHz$

VSWR 20:1 at 140W pulse CW Output Power	No Device Degradation
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Package Outline

Flanged ceramic package; 2 mounting holes; 4 leads



OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-LB/LBB					05/21/2021